

AWT6275

HELP™ IMT/WCDMA 3.4V/27.5dBm Linear Power Amplifier Module Data Sheet - Rev 2.2

FEATURES

- InGaP HBT Technology
- · High Efficiency:

43% @ Pout = +27.5 dBm

21% @ Pout = +16 dBm

15% @ Роит = +7 dВm

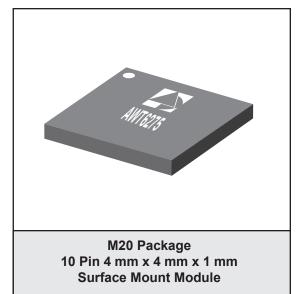
- Low Quiescent Current: 16 mA
- Low Leakage Current in Shutdown Mode:<1 mA
- VREF = +2.85 V (+2.75 V min over temp)
- Optimized for a 50 Ω System
- Low Profile Miniature Surface Mount Package
- RoHS Compliant Package, 250 °C MSL-3
- HSPA Capable

APPLICATIONS

 WCDMA/HSPA IMT-Band Wireless Handsets and Data Devices

PRODUCT DESCRIPTION

The AWT6275 meets the increasing demands for higher output power in UMTS handsets. The PA module is optimized for VREF = +2.85 V, a requirement for compatibility with the Qualcomm® 6250 chipset. The device is manufactured on an advanced InGaP HBT MMIC technology offering state-of-the-art reliability, temperature stability, and ruggedness. Selectable bias modes that optimize efficiency for different output power levels, and a



shutdown mode with low leakage current, increase handset talk and standby time. The self-contained 4 mm x 4 mm x 1 mm surface mount package incorporates matching networks optimized for output power, efficiency, and linearity in a 50 Ω system.

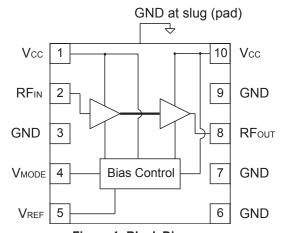


Figure 1: Block Diagram

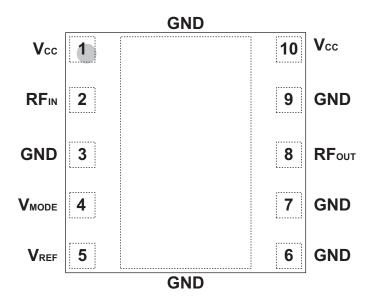


Figure 2: Pinout (X-ray Top View)

Table 1: Pin Description

PIN	NAME	DESCRIPTION	
1	Vcc	Supply Voltage	
2	RFℕ	RF Input	
3	GND	Ground	
4	V _{MODE}	Mode Control Voltage	
5	V_{REF}	Reference Voltage	
6	GND	Ground	
7	GND	Ground	
8	RFout	RF Output	
9	GND	Ground	
10	Vcc	Supply Voltage	

ELECTRICAL CHARACTERISTICS

Table 2: Absolute Minimum and Maximum Ratings

PARAMETER	MIN	MAX	UNIT
Supply Voltage (Vcc)	0	+5	V
Mode Control Voltage (VMODE)	0	+3.5	V
Reference Voltage (VREF)	0	+3.5	V
RF Input Power (Pℕ)	ı	+10	dBm
Storage Temperature (Tstg)	-40	+150	°C

Table 3: Operating Ranges

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Operating Frequency (f)	1920	-	1980	MHz	
Supply Voltage (Vcc)	+3.2	+3.4 +1.5	+4.2	V	Pouτ ≤ +27.5 dBm Pouτ ≤ 7 dBm
Reference Voltage (V _{REF})	+2.75 0	+2.85	+2.95 +0.5	V	PA "on" PA "shut down"
Mode Control Voltage (VMODE)	+2.3 0	+2.85	+3.1 +0.5	V	Low Bias Mode High Bias Mode
RF Output Power (Pout) R99 WCDMA, HPM HSPA (MPR=0), HPM R99 WCDMA, LPM HSPA (MPR=0), LPM	27 ⁽¹⁾ 26 ⁽¹⁾ 15.5 ⁽¹⁾ 14.5 ⁽¹⁾	27.5 26.5 16 15	27.5 26.5 16 15	dBm	3GPP TS 34.121-1, Rel 7 Table C.11.1.3
Case Temperature (Tc)	-20	-	+90	°C	

The device may be operated safely over these conditions; however, parametric performance is guaranteed only over the conditions defined in the electrical specifications.

Notes:

(1) For operation at $V_{\rm CC}$ = +3.2 V, $P_{\rm OUT}$ is derated by 0.5 dB.



Table 4: Electrical Specifications (Tc = +25 °C, Vcc = +3.4 V, V_{REF} = +2.85 V, 50 Ω system)

PARAMETER	MIN	TYP	MAX	UNIT	COMMENTS
Gain	24.5 13.5 12	26.5 15.5 14	29 17.5 16	dB	Pout = +27.5 dBm, V _{MODE} = 0 V Pout = +16 dBm, V _{MODE} = +2.85 V Pout = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V
ACLR1 at 5 MHz offset (1)		-41 -43 -40	-38 -38 -38	dBc	Pout = +27.5 dBm, V _{MODE} = 0 V Pout = +16 dBm, V _{MODE} = +2.85 V Pout = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V
ACLR2 at 10 MHz offset	- - -	-58 -52 -57	-48 -48 -48	dBc	Pout = +27.5 dBm, V _{MODE} = 0 V Pout = +16 dBm, V _{MODE} = +2.85 V Pout = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V
Power-Added Efficiency (1)	39 18 12	43 21 15	- - -	%	Pout = +27.5 dBm, V _{MODE} = 0 V Pout = +16 dBm, V _{MODE} = +2.85 V Pout = +7 dBm, V _{CC} = 1.5 V, V _{MODE} = +2.85 V
Quiescent Current (lcq)	-	16	22	mA	V _{MODE} = +2.85 V, V _{CC} = 3.4 V
Reference Current	-	3.6	7	mA	through V _{REF} pin
Mode Control Current	-	0.3	1	mA	through V _{MODE} pin, V _{MODE} = +2.85 V
Leakage Current	-	<1	5	μA	V _{CC} = +4.2 V, V _{REF} = 0 V, V _{MODE} = 0 V
Noise in Receive Band	-	-141	-138	dBm/Hz	2110 MHz to 2170 MHz
Harmonics 2fo 3fo, 4fo	1 1	-45 -50	-40 -45	dBc	Роит <u><</u> +27.5 dВm
Input Impedance	-	-	2:1	VSWR	
Spurious Output Level (all spurious outputs)	-	-	-70	dBc	Pout ≤ +27.5 dBm In-band load VSWR < 5:1 Out-of-band load VSWR < 10:1 Applies over all operating conditions
Load mismatch stress with no permanent degradation or failure	10:1	-	_	VSWR	Applies over full operating range

Notes

(1) ACLR and Efficiency measured at 1950 MHz.

APPLICATION INFORMATION

To ensure proper performance, refer to all related Application Notes on the ANADIGICS web site: http://www.anadigics.com

Shutdown Mode

The power amplifier may be placed in a shutdown mode by applying logic low levels (see Operating Ranges table) to the VREF and VMODE voltages.

Bias Modes

The power amplifier may be placed in either a Low Bias mode or a High Bias mode by applying the appropriate logic level (see Operating Ranges table) to VMODE

voltage. The Bias Control table lists the recommended modes of operation for various applications.

Three operating modes are recommended to optimize current consumption. High Bias/High Power operating mode is for PouT levels \geq 16 dBm. At \sim 16 dBm - 7 dBm, the PA should be "Mode Switched" to Low Bias Mode. For PouT levels < \sim 7 dBm, the Vcc can be switched to 1.5 V (Low Bias Mode is also used for PouT range).

Table 6: Bias Control

APPLICATION	P _{OUT} LEVELS	BIAS MODE	VREF	V _{MODE}	Vcc
WCDMA - low power	<u><</u> +7 dBm	Low	+2.85 V	+2.85 V	<u>></u> +1.5
WCDMA - med power	7 <u><</u> Ро∪т <u><</u> +16 dВm	Low	+2.85 V	+2.85 V	+3.4
WCDMA - high power	>+16 dBm	High	+2.85 V	0 V	+3.4
Shutdown	-	Shutdown	0 V	0 V	-

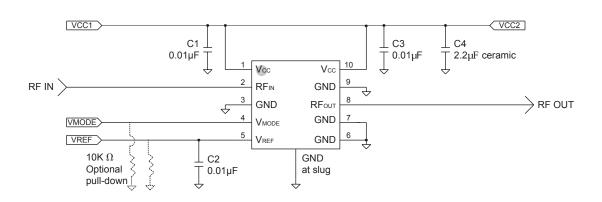
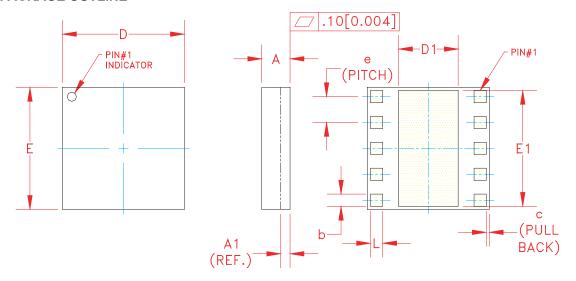


Figure 3: Application Circuit



PACKAGE OUTLINE



*\ <u></u>	MILLIMETERS				NOTE		
_٩.	MN.	NOM.	MAX.	MN.	NOM.	MAX.	1,112
Α	0.88	0.98	1.08	0.034	0.038	0.042	-
A1	0.32 (REF.)			0.0	0.0125 (REF.)		
ь	0.35	-	0.60	0.013	-	0.024	3
С	-	0.10	-	-	0.004	-	-
D	3.88	4.00	4.12	0.152	0.157	0.162	_
D1	1.90	_	2.25	0.075	_	0.088	_
Ε	3.88	4.00	4.12	0.152	0.157	0.162	_
E1	3.75	_	3.85	0.148	_	0.152	-
8		0.85			0.033		3
L	0.35	_	0.60	0.013	_	0.024	3

NOTES:

- 1. CONTROLLING DIMENSIONS: MILLIMETERS
 2. UNLESS SPECIFIED TOLERANCE=±0.076[0.003].
 3. PADS (INCLUDING CENTER) SHOWN UNIFORM SIZE FOR REFERENCE ONLY.

Figure 4: Package Outline - 10 Pin 4 mm x 4 mm x 1 mm Surface Mount Module



NOTES:

1. ANADIGICS LOGO SIZE: X=0.040±0.010 Y=0.048±0.010

2. PART # AWT6275R

3. YEAR AND WORK WEEK: YYWW: YY = YEAR, WW = WORK WEEK

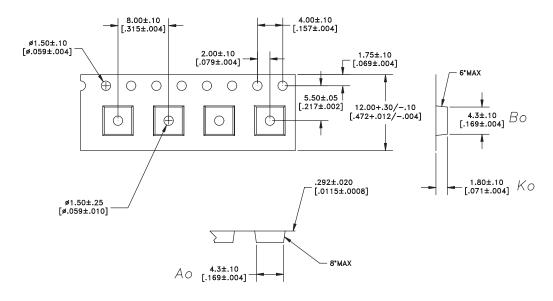
4. LOT - WAFER I.D.: LLLLL - SS = WAFER/LOT I.D.5. PIN 1 INDICATOR: MOLD NOTCH -or- INK DOT

6. BOM # BBB

7. COUNTRY CODE: CCCCCC

8. TYPE : ELITE SIZE : AS LARGE AS POSSIBLE LASER MARKED

Figure 5: Branding Specification



DIMENSIONS ARE IN MILLIMETERS [INCHES]
STANDARD TOLERANCES

Figure 6: Tape & Reel Packaging

Table 6: Tape & Reel Dimensions

PACKAGE TYPE	TAPE WIDTH	POCKET PITCH	REEL CAPACITY	MAX REEL DIA
4 mm x 4 mm x 1 mm	12 mm	8 mm	2500	13"

AWT6275

ORDERING INFORMATION

ORDER NUMBER	TEMPERATURE RANGE	PACKAGE DESCRIPTION	COMPONENT PACKAGING
AWT6275RM20P8	-20 °C to +90 °C	RoHS Compliant 10 Pin 4 mm x 4 mm x 1 mm Surface Mount Module	Tape and Reel, 2500 pieces per Reel
AWT6275RM20P9 -20 °C to +90 °C 4 mm x 4		RoHS Compliant 10 Pin 4 mm x 4 mm x 1 mm Surface Mount Module	Partial Tape and Reel



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